

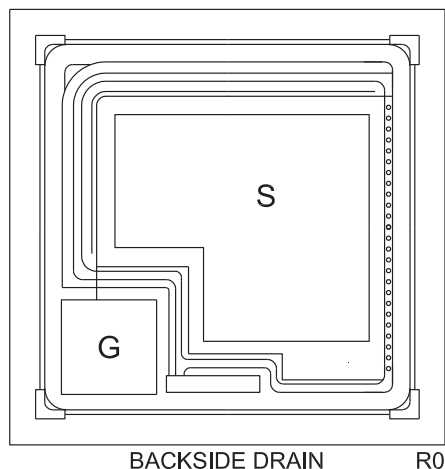
PROCESS CP394R
Small Signal MOSFET Transistor
N-Channel Enhancement-Mode Transistor Chip



PROCESS DETAILS

Die Size	15.7 x 15.7 MILS
Die Thickness	3.9 MILS
Gate Bonding Pad Area	3.9 x 3.9 MILS
Source Bonding Pad Area	9.1 x 8.1 MILS
Top Side Metalization	Al-Si - 35,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



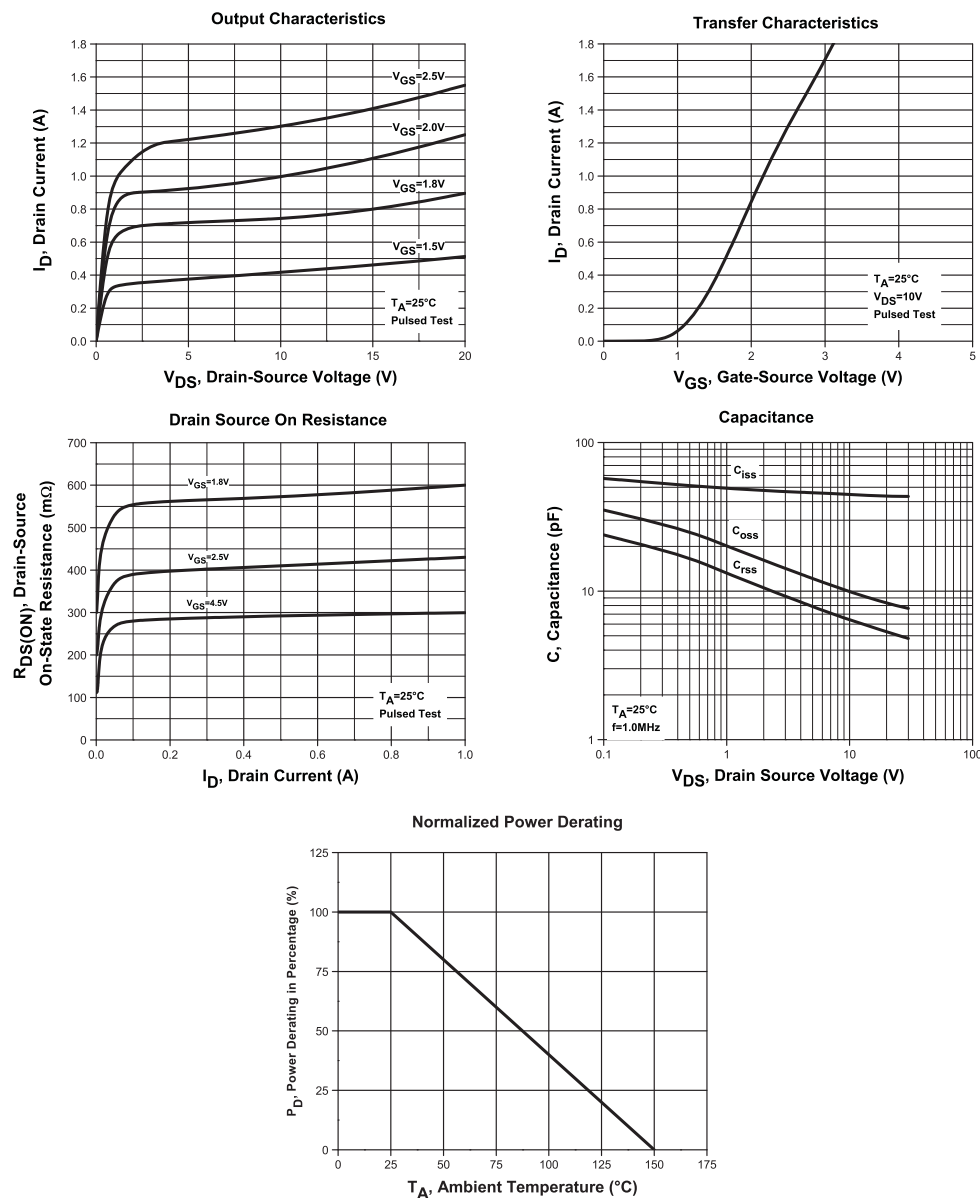
GROSS DIE PER 6 INCH WAFER
95,400

PRINCIPAL DEVICE TYPES
CEDM7004

R1 (22-March 2010)

PROCESS CP394R

Typical Electrical Characteristics



R1 (22-March 2010)